

## Features

1024Kx32 bit CMOS Static

Random Access Memory

- Access Times: 12, 15ns
- Individual Byte Selects
- Fully Static, No Clocks
- TTL Compatible I/O

High Density Package

- 72 lead SIMM, No. 176 (Angle)
- 72 lead SIMM, No. 356 (Straight)
- Common Data Inputs and Outputs

Single +5V ( $\pm 10\%$ ) Supply Operation

## 1024Kx32 Static RAM

### CMOS, High Speed Module

The EDI8F321024CA is a high speed 32 megabit Static RAM module organized as 1024K words by 32 bits. This module is constructed from eight 1024Kx4 Static RAMs in SOJ packages on an epoxy laminate (FR4) board.

Four chip enables ( $\overline{E0}$ - $\overline{E3}$ ) are used to independently enable the four bytes. Reading or writing can be executed on individual bytes or any combination of multiple bytes through proper use of selects.

The EDI8F321024CA is offered in a 72 lead SIMM package, which enable 32 megabits of memory to be placed in less than 1.3 square inches of board space.

All inputs and outputs are TTL compatible and operate from a single 5V supply. Fully asynchronous circuitry requires no clocks or refreshing for operation and provides equal access and cycle times for ease of use.

Pins PD1- PD4, are used to identify module memory density in applications where alternate modules can be interchanged.

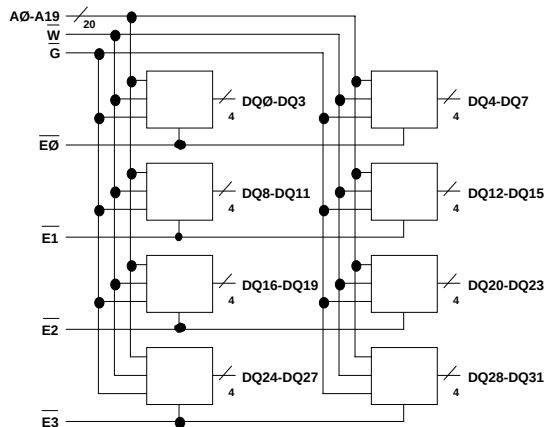
## Pin Configurations and Block Diagram

|      |    |    |      |
|------|----|----|------|
| NC   | 2  | 1  | NC   |
| PD4  | 4  | 3  | PD3  |
| PD1  | 6  | 5  | VSS  |
| DQ0  | 8  | 7  | PD2  |
| DQ1  | 10 | 9  | DQ8  |
| DQ2  | 12 | 11 | DQ9  |
| DQ3  | 14 | 13 | DQ10 |
| VCC  | 16 | 15 | DQ11 |
| A7   | 18 | 17 | A0   |
| A8   | 20 | 19 | A1   |
| A9   | 22 | 21 | A2   |
| DQ4  | 24 | 23 | DQ12 |
| DQ5  | 26 | 25 | DQ13 |
| DQ6  | 28 | 27 | DQ14 |
| DQ7  | 30 | 29 | DQ15 |
| W    | 32 | 31 | VSS  |
| A14  | 34 | 33 | A15  |
| E0   | 36 | 35 | E1   |
| E2   | 38 | 37 | E3   |
| A16  | 40 | 39 | A17  |
| VSS  | 42 | 41 | G    |
| DQ16 | 44 | 43 | DQ24 |
| DQ17 | 46 | 45 | DQ25 |
| DQ18 | 48 | 47 | DQ26 |
| DQ19 | 50 | 49 | DQ27 |
| A10  | 52 | 51 | A3   |
| A11  | 54 | 53 | A4   |
| A12  | 56 | 55 | A5   |
| A13  | 58 | 57 | VCC  |
| DQ20 | 60 | 59 | A6   |
| DQ21 | 62 | 61 | DQ28 |
| DQ22 | 64 | 63 | DQ29 |
| DQ23 | 66 | 65 | DQ30 |
| VSS  | 68 | 67 | DQ31 |
| A19  | 70 | 69 | A18  |
| NC   | 72 | 71 | NC   |

PD1 & PD3 = VSS  
PD2 & PD4 = Open

## Pin Names

|          |                          |
|----------|--------------------------|
| A0-A19   | Address Inputs           |
| E0-E3    | Chip Enables             |
| W        | Write Enable             |
| G        | Output Enable            |
| DQ0-DQ31 | Common Data Input/Output |
| VCC      | Power (+5V $\pm 10\%$ )  |
| VSS      | Ground                   |
| NC       | No Connection            |



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### Absolute Maximum Ratings\*

|                                    |                 |
|------------------------------------|-----------------|
| Voltage on any pin relative to VSS | -0.5V to 7.0V   |
| Operating Temperature TA (Ambient) |                 |
| Commercial                         | 0°C to +70°C    |
| Industrial                         | -40°C to +85°C  |
| Storage Temperature, Plastic       | -55°C to +125°C |
| Power Dissipation                  | 7.0 Watts       |
| Output Current                     | 20 mA           |

\*Stress greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions greater than those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

### Recommended DC Operating Conditions

| Parameter          | Sym | Min  | Typ | Max | Units |
|--------------------|-----|------|-----|-----|-------|
| Supply Voltage     | VCC | 4.5  | 5.0 | 5.5 | V     |
| Supply Voltage     | VSS | 0    | 0   | 0   | V     |
| Input High Voltage | VIH | 2.2  | --  | 6.0 | V     |
| Input Low Voltage  | VIL | -0.3 | --  | 0.8 | V     |

### AC Test Conditions

|                                |                 |
|--------------------------------|-----------------|
| Input Pulse Levels             | VSS to 3.0V     |
| Input Rise and Fall Times      | 5ns             |
| Input and Output Timing Levels | 1.5V            |
| Output Load                    | 1TTL, CL = 30pF |

(note: For TEHQZ, TGHQZ and TWLQZ, CL = 5pF)

### DC Electrical Characteristics

| Parameter                          | Sym  | Conditions                                            | Min | Typ | Max  | Units |
|------------------------------------|------|-------------------------------------------------------|-----|-----|------|-------|
| Operating Power Supply Current     | ICC1 | $\bar{W}, \bar{E} = VIL, I/O = 0mA, \text{Min Cycle}$ |     |     | 1600 | mA    |
| Standby (TTL) Power Supply Current | ICC2 | $\bar{E}^3 VIH, VIN \nless VIL \text{ or } VIN^3 VIH$ |     |     | 600  | mA    |
| Full Standby Power Supply Current  | ICC3 | $\bar{E}^3 VCC-0.2V$                                  |     |     | 90   | mA    |
| CMOS                               |      | $VIN^3 VCC-0.2V \text{ or } VIN \nless 0.2V$          |     |     |      |       |
| Input Leakage Current              | ILI  | $VIN = 0V \text{ to } VCC$                            | --  | --  | ±80  | μA    |
| Output Leakage Current             | ILO  | $V I/O = 0V \text{ to } VCC$                          | --  | --  | ±20  | μA    |
| Output High Voltage                | VOH  | $IOH = -4.0mA$                                        | 2.4 | --  | --   | V     |
| Output Low Voltage                 | VOL  | $IOL = 8.0mA$                                         | --  | --  | 0.4  | V     |

\*Typical: TA = 25°C, VCC = 5.0V

### Truth Table

| $\bar{E}$ | $\bar{W}$ | $\bar{G}$ | Mode     | Output | Power     |
|-----------|-----------|-----------|----------|--------|-----------|
| H         | X         | X         | Standby  | HIGH Z | ICC2/ICC3 |
| L         | H         | L         | Read     | DOUT   | ICC1      |
| L         | L         | X         | Write    | DIN    | ICC1      |
|           |           |           | Output   |        |           |
| L         | H         | H         | Deselect | HIGH Z | ICC1      |

### Capacitance

(f=1.0MHz, VIN=VCC or VSS)

| Parameter        | Sym  | Max | Unit |
|------------------|------|-----|------|
| Address Lines    | CI   | 60  | pF   |
| Data Lines       | CD/Q | 20  | pF   |
| Chip Enable Line | CC   | 20  | pF   |
| Write Line       | CN   | 60  | pF   |

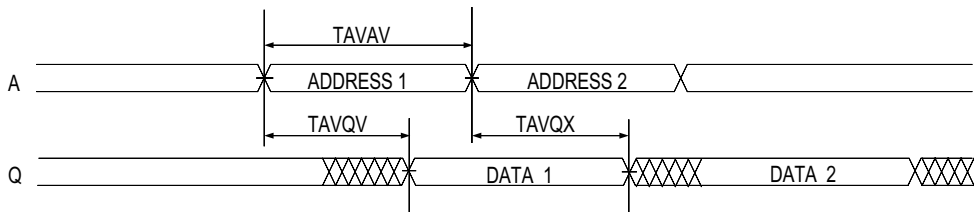
These parameters are sampled, not 100% tested.

### AC Characteristics Read Cycle

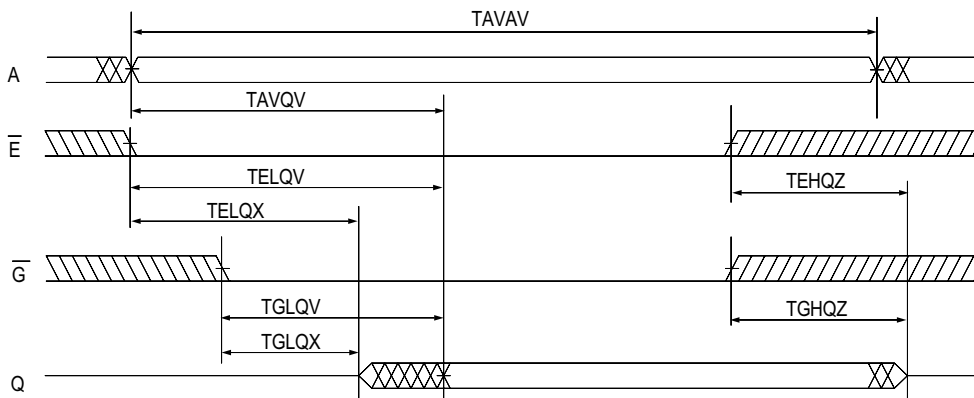
| Parameter                             | Symbol |      | 12ns |     | 15ns |     | Units |
|---------------------------------------|--------|------|------|-----|------|-----|-------|
|                                       | JEDEC  | Alt. | Min  | Max | Min  | Max |       |
| Read Cycle Time                       | TAVAV  | TRC  | 12   |     | 15   |     | ns    |
| Address Access Time                   | TAVQV  | TAA  |      | 12  |      | 15  | ns    |
| Chip Enable Access                    | TELQV  | TACS |      | 12  |      | 15  | ns    |
| Chip Enable to Output in Low Z (1)    | TELQX  | TCLZ | 3    |     | 3    |     | ns    |
| Chip Disable to Output in High Z (1)  | TEHQZ  | TCHZ |      | 6   |      | 7   | ns    |
| Output Hold from Address Change       | TAVQX  | TOH  | 3    |     | 3    |     | ns    |
| Output Enable to Output Valid         | TGLQV  | TOE  |      | 6   |      | 7   | ns    |
| Output Enable to Output in Low Z (1)  | TGLQX  | TOLZ | 0    |     | 0    |     | ns    |
| Output Disable to Output in High Z(1) | TGHQZ  | TOHZ |      | 6   |      | 7   | ns    |

Note 1: Parameter guaranteed, but not tested.

### Read Cycle 1 - W High, $\bar{G}$ , $\bar{E}$ Low



### Read Cycle 2 - W High

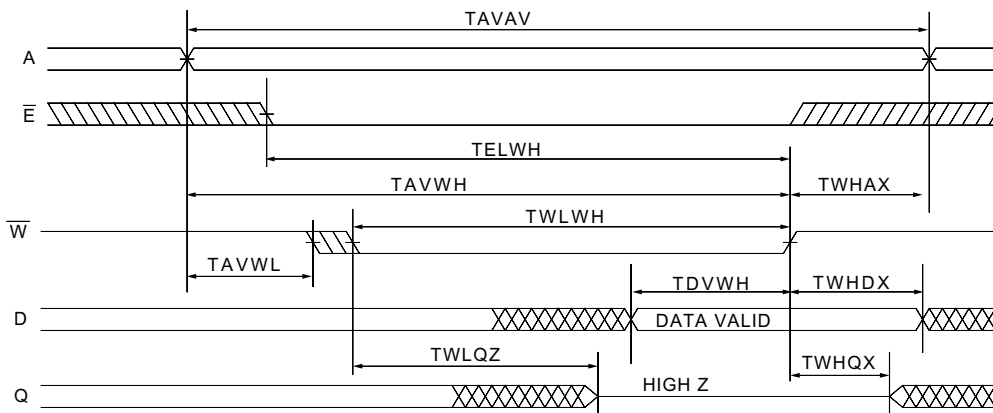


## AC Characteristics Write Cycle

| Parameter                           | Symbol |      | 15ns |     | 17ns |     | Units |
|-------------------------------------|--------|------|------|-----|------|-----|-------|
|                                     | JEDEC  | Alt. | Min  | Max | Min  | Max |       |
| Write Cycle Time                    | TAVAV  | TWC  | 15   |     | 15   |     | ns    |
| Chip Enable to End of Write         | TELWH  | TCW  | 10   |     | 12   |     | ns    |
|                                     | TWLEH  | TCW  | 10   |     | 12   |     | ns    |
| Address Setup Time                  | TAVWL  | TAS  | 0    |     | 0    |     | ns    |
|                                     | TAVEL  | TAS  | 0    |     | 0    |     | ns    |
| Address Valid to End of Write       | TAVWH  | TAW  | 10   |     | 12   |     | ns    |
|                                     | TAVEH  | TAW  | 10   |     | 12   |     | ns    |
| Write Pulse Width                   | TWLWH  | TWP  | 10   |     | 12   |     | ns    |
|                                     | TELEH  | TWP  | 10   |     | 12   |     | ns    |
| Write Recovery Time                 | TWHAX  | TWR  | 0    |     | 0    |     | ns    |
|                                     | TEHAX  | TWR  | 0    |     | 0    |     | ns    |
| Data Hold Time                      | TWHDX  | TDH  | 0    |     | 0    |     | ns    |
|                                     | TEHDX  | TDH  | 0    |     | 0    |     | ns    |
| Write to Output in High Z (1)       | TWLQZ  | TWHZ | 0    | 7   | 0    | 8   | ns    |
| Data to Write Time                  | TDVWH  | TDW  | 7    |     | 10   |     | ns    |
|                                     | TDVEH  | TDW  | 7    |     | 10   |     | ns    |
| Output Active from End of Write (1) | TWHQX  | TWLZ | 3    |     | 3    |     | ns    |

Note 1: Parameter guaranteed, but not tested.

## Write Cycle 1 - $\bar{W}$ Controlled



**Write Cycle 2 -  $\bar{E}$  Controlled**

